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SLLSEA6B - DECEMBER 2011 - REVISED JUNE 2012

LOW-POWER CAN TRANSCEIVER WITH BUS WAKE-UP

Check for Samples: SN65HVD1040-HT

FEATURES

- Improved Drop-in Replacement for the TJA1040
- ±12 kV ESD Protection
- Low-Current Standby Mode with Bus Wake-up:
 5 μA Typical
- Bus-Fault Protection of –27 V to 40 V
- Rugged Split-Pin Bus Stability
- Dominant Time-Out Function
- Thermal Shutdown Removed
- Power-Up/Down Glitch-Free Bus Inputs and Outputs
 - High Input Impedance with Low V_{CC}
 - Monotonic Outputs During Power Cycling
- DeviceNet Vendor ID # 806

APPLICATIONS

- Down-Hole Drilling
- High Temperature Environments
- Vibration/Modal Analysis
- Multi-Channel Data Acquisition
- Acoustics/Dynamic Strain Gauges
- Pressure Sensors

SUPPORTS EXTREME TEMPERATURE APPLICATIONS

- Controlled Baseline
- One Assembly/Test Site
- · One Fabrication Site
- Available in Extreme (-55°C/210°C)
 Temperature Range (1)
- Extended Product Life Cycle
- Extended Product-Change Notification
- Product Traceability
- Texas Instruments high temperature products utilize highly optimized silicon (die) solutions with design and process enhancements to maximize performance over extended temperatures. All devices are characterized and qualified for 1000 hours continuous operating life at maximum rated temperature.

(1) Custom temperature ranges available

DESCRIPTION

The SN65HVD1040 meets or exceeds the specifications of the ISO 11898 standard for use in applications employing a Controller Area Network (CAN). As CAN transceivers, these devices provide differential transmit and receive capability for a CAN controller at signaling rates of up to 1 megabit per second (Mbps). (2)

Designed for operation in especially harsh environments, the device features ±12 kV ESD protection on the bus and split pins, cross-wire, overvoltage and loss of ground protection from -27 to 40 V, a -12 V to 12 V common-mode range, and will withstand voltage transients from -200 V to 200 V according to ISO 7637.

The STB input (pin 8) selects between two different modes of operation; high-speed or low-power mode. The high-speed mode of operation is selected by connecting STB to ground.

If a high logic level is applied to the STB pin of the SN65HVD1040, the device enters a low-power bus-monitor standby mode. While the SN65HVD1040 is in the low-power bus-monitor standby mode, a dominant bit greater than 5 µs on the bus is passed by the bus-monitor circuit to the receiver output. The local protocol controller may then reactivate the device when it needs to transmit to the bus.

A dominant-time-out circuit in the SN65HVD1040 prevents the driver from blocking network communication during a hardware or software failure. The time-out circuit is triggered by a falling edge on TXD (pin 1). If no rising edge is seen before the time-out constant of the circuit expires, the driver is disabled. The circuit is then reset by the next rising edge on TXD.

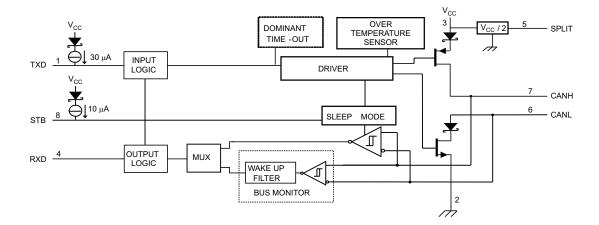
(2) The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



The SPLIT output (pin 5) is available on the SN65HVD1040 as a $V_{\rm CC}/2$ common-mode bus voltage bias for a split-termination network.

The SN65HVD1040 is characterized for operation from -55°C to 210°C.







This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

Table 1. ORDERING INFORMATION⁽¹⁾

T _J	PACKAGE	ORDERABLE PART NUMBER	TOP-SIDE MARKING
−55°C to 210°C	KGD (bare die)	SN65HVD1040SKGD3	NA
–55°C to 175°C	D	SN65HVD1040HD	H1040

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

BARE DIE INFORMATION

DIE THICKNESS	BACKSIDE FINISH	BACKSIDE POTENTIAL	BOND PAD METALLIZATION COMPOSITION	BOND PAD THICKNESS
15 mils.	Silicon with backgrind	Floating	CuNiPd	15 microns

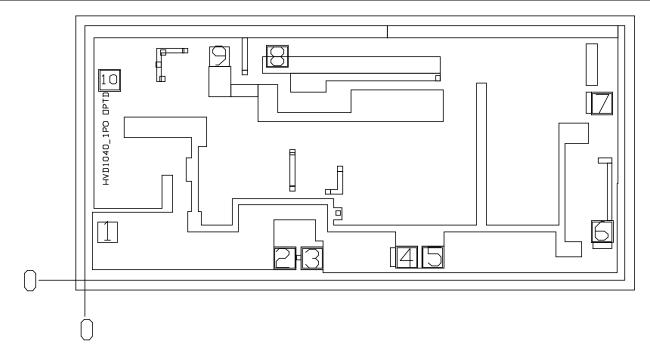


Table 2. BOND PAD COORDINATES (µm)

DESCRIPTION	PAD NUMBER	X MIN	Y MIN	X MAX	Y MAX	PAD SIZE X	PAD SIZE Y
TXD	1	53.64	162	137.7	246.06	84.06	84.06
GND	2	804.06	50.85	888.12	134.91	84.06	84.06
GND	3	920.07	50.85	1004.13	134.91	84.06	84.06
Vcc	4	1320.21	54.18	1404.27	138.24	84.06	84.06
Vcc	5	1431.09	54.18	1515.15	138.24	84.06	84.06
RXD	6	2148.75	164.34	2232.81	248.4	84.06	84.06
SPLIT	7	2147.4	707.49	2231.46	791.55	84.06	84.06
CANL	8	771.93	907.38	855.99	991.44	84.06	84.06
CANH	9	527.31	907.38	611.37	991.44	84.06	84.06
STB	10	62.28	806.13	146.34	890.19	84.06	84.06

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ABSOLUTE MAXIMUM RATINGS(1)

				VALUE				
V _{CC}	Supply voltage (2)			–0.3 V to 7 V				
V _{I(bus)}	Voltage range at any but	s terminal (CANH, CANL, SPLI	T)	–27 V to 40 V				
I _{O(OUT)}	Receiver output current			-20 mA to 20 mA				
	Voltage input, transient p	Voltage input, transient pulse ⁽³⁾ , (CANH, CANL, SPLIT)						
	IEC Contact Discharge	(IEC 61000-4-2)	Bus terminals vs GND	±6 kV				
	Lluman hadu madal	JEDEC Standard 22,	Bus terminals vs GND	±12 kV				
ESD	Human body model	Test Method A114-C.01	All pins	±4 kV				
	Field-Induced-Charged Device Model	JEDEC Standard 22, Test Method C101	All pins	±1 kV				
	Machine model	ANSI/ESDS5.2-1996		±200 V				
IEC			Bus terminals vs GND	±6 kV				
VI	Voltage input range (TXI	D, STB)		–0.5 V to 6 V				
T_{J}	Junction temperature			–55°C to 210°C				

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL CHARACTERISTICS FOR HKQ PACKAGE

over operating free-air temperature range (unless otherwise noted)

	PARAME	TER	MIN	TYP	MAX	UNIT
Δ	lunction to cope thermal registeres	to ceramic side of case			5.7	°C/W
₽ ^{JC}	Junction-to-case thermal resistance	to top of case lid (metal side of case)		13.7	C/VV	

THERMAL INFORMATION FOR D PACKAGE

		SN65HVD1040	
	THERMAL METRIC ⁽¹⁾	D	UNITS
		8 PINS	
θ_{JA}	Junction-to-ambient thermal resistance (2)	91.9	
θ_{JCtop}	Junction-to-case (top) thermal resistance (3)	39.9	
θ_{JB}	Junction-to-board thermal resistance ⁽⁴⁾	40.6	90044
Ψ_{JT}	Junction-to-top characterization parameter ⁽⁵⁾	3.9	°C/W
ΨЈВ	Junction-to-board characterization parameter ⁽⁶⁾	39.6	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance (7)	N/A	

- (1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter, ψ_{JT}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

⁽²⁾ All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

⁽³⁾ Tested in accordance with ISO 7637, test pulses 1, 2, 3a, 3b, 5, 6 & 7.



RECOMMENDED OPERATING CONDITIONS

			$T_{\rm J} = -5$	5°C to 12	25°C	$T_{\rm J} = -5$	5°C to 17	5°C	T _J = -	UNIT		
			MIN	NOM	MAX	MIN	NOM	MAX	MIN	NOM	MAX	UNII
V_{CC}	Supply voltage		4.75		5.25	4.75		5.25	4.75		5.25	٧
V_{IC} or V_{IC}	Voltage at any bus or common mode)	terminal (separately	-12 ⁽¹⁾		12	-12 ⁽¹⁾		12	-12 ⁽¹⁾		12	٧
V _{IH}	High-level input voltage	TVD CTD	2		5.25	2		5.25	2		5.25	٧
V _{IL}	Low-level input voltage	t TXD, STB	0		0.8	0		8.0	0		0.8	٧
V_{ID}	Differential input vo	ltage	-6		6	-6		6	-6		6	V
	High-level output	Driver	-70			-70			-70			∞ Λ
I _{OH}	current	Receiver	-2			-2			-2			mA
	Low-level output	Driver			70			70			70	∞ ^
I _{OL}	current	Receiver			2			2			2	mA
t _{SS}	Maximum pulse width to remain in standby				0.7			0.7			0.7	μs
TJ	Junction temperatur	re	-55		125	– 55		175	– 55		210	ç

⁽¹⁾ The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet.

SUPPLY CURRRENT

over operating free-air temperature range (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	$T_{\rm J} = -5$	5°C to 1	25°C	T _J = -5	T _J = -55°C to 175°C			5°C to 2	10°C	UNIT
			TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNII
		Domina nt	$V_I = 0 \text{ V}, 60 \Omega \text{ Load},$ STB at 0 V		50	70		50	70		50	70	A
I _{CC}	$\begin{array}{c} \text{Supply} \\ \text{I}_{\text{CC}} \text{current,} \\ \text{V}_{\text{CC}} \end{array}$	Recessi ve	$V_I = V_{CC}$, STB at 0 V		6	10		6	10		6	10	mA
	•66	Standby	STB at VCC, VI = VCC		5	12		5	20		5	50	μΑ

DEVICE SWITCHING CHARACTERISTICS

over recommended operating conditiions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	$T_J = -$	55°C to 1	25°C	$T_{\rm J} = -5$	5°C to 17	75°C	T _J = -55°C to 210°C			UNIT
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
t _{loop}	Total loop delay, driver input to receiver output, Recessive to Dominant	STB at 0 V.	90		230	90		325	90		450	
t _{loop} 2	Total loop delay, driver input to receiver output, Dominant to Recessive	See Figure 10	90		230	90		325	90		450	ns

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DRIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditiions (unless otherwise noted)

		_	TEGT GONDITIONS	$T_{\rm J} = -5$	5°C to 12	5°C	$T_{\rm J} = -5$	5°C to 17	′5°C	$T_J =$	-55°C to 2	10°C	
P	ARAMETE	K	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	MIN	TYP ⁽¹⁾	MAX	MIN	TYP ⁽¹⁾	MAX	UNIT
	Bus output	CAN H	$V_I = 0 \text{ V}, \text{ STB at } 0 \text{ V}, \text{ R}_L =$	2.9	3.4	4.5	2.9	3.4	4.6	2.9	3.4	4.6	
V _{O(D)}	voltage (Domina nt)	CANL	60 Ω, See Figure 2 and Figure 3	0.8		1.75	0.8		1.75	0.8		1.75	V
$V_{O(R)}$	Bus output voltage (Recessive		V _I = 3 V, STB at 0 V, See Figure 2 and Figure 3	2	2.5	3	2	2.5	3	2	2.5	3	٧
Vo	Bus output voltage (S		$R_L = 60 \Omega$, STB at V_{CC} , See Figure 2 and Figure 3	-0.1		0.1	-0.125		0.125	-0.15		0.15	>
V	Differentia	l output	$V_I = 0 \text{ V}, R_L = 60 \Omega, STB$ at 0 V, See Figure 2 and Figure 3, and Figure 4	1.5		3	1.5		3	1.5		3	V
V _{OD(D)}	voltage (Dominant	·)	$V_I = 0 \text{ V}, R_L = 45 \Omega, \text{ STB}$ at 0 V, See Figure 2 and Figure 3	1.4		3	1.4		3	1.4		3	V
V_{SYM}	Output syr (Dominant Recessive [V _{O(CANH)} V _{O(CANL)}]	or)	STB at 0 V, See Figure 3 and Figure 14	0.9×V _{CC}	V _{cc}	1.1×V _C	0.9×V _{CC}	V _{cc}	1.1×V _C	0.9×V _C	V _{cc}	1.2×V _{CC}	٧
$V_{OD(R)}$	Differentia voltage	l output	$V_I = 3 \text{ V}, R_L = 60 \Omega, \text{ STB}$ at 0 V, See Figure 2 and Figure 3	-0.012		0.012	-0.014		0.017	-0.015		0.02	V
OD(II)	(Recessive	e)	V _I = 3 V, STB at 0 V, No Load	-0.5		0.05	-0.5		0.225	-0.75		0.8	
V _{OC(D)}	Common-routput volt (Dominant	age		2	2.3	3	2	2.3	3	2	2.3	3.1	V
V _{OC(pp}	Peak-to-pe common-n output volt	node	STB at 0 V, See Figure 9		0.3			0.3			0.3		V
I _{IH}	High-level current, TX input		V _I at V _{CC}	-2		2	-3		3	-3		3	μΑ
I _{IL}	Low-level current, TX input		V _I at 0 V	-50		-10	-50		-10	-50		-10	μA
I _{O(off)}	Power-off Leakage o		V _{CC} at 0 V, TXD at 5 V			1			180			600	μΑ
			V _{CANH} = -12 V, CANL Open, See Figure 13	-120	-72		-120	-72		-130	-72		
	Short-circu		V _{CANH} = 12 V, CANL Open, See Figure 13		0.36	1		0.36	1		0.36	1.1	m^
IOS(ss)	steady-sta output cur	rent	V _{CANL} = -12 V, CANH Open, See Figure 13	-1	-0.5		-1	-0.5		-1.1	-0.5		mA
			V _{CANL} = 12 V, CANH Open, See Figure 13		71	120		71	120		71	130	
Co	Output capacitano	ce	See Input capacitance to ground in RECEIVER ELECTRICAL CHARACTERISTICS.										

⁽¹⁾ All typical values are at 25°C with a 5-V supply.



DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	DADAMETED	TEST CONDITIONS	$T_{\rm J} = -5$	5°C to 12	25°C	$T_{\rm J} = -5$	5°C to 1	75°C	$T_{\rm J} = -5$	5°C to	210°C	UNIT
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNII
t _{PLH}	Propagation delay time, low-to-high-level output		25	65	120	25	65	175	25	65	250	
t _{PHL}	Propagation delay time, high-to-low-level output		25	45	120	25	45	175	25	45	250	
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})	STB at 0 V, See Figure 5			25		25				25	ns
t _r	Differential output signal rise time			25			25			25		
t _f	Differential output signal fall time			50			50			50		
t _{en}	Enable time from silent mode to dominant	See Figure 8			11			14.5			18	μs
t _{dom}	Dominant time-out	See Figure 11	300	450	700	300	450	700	300	450	700	μs



RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	DADAME	TED	TEST COMPLETIONS	$T_{\rm J} = -5$	5°C to 1	25°C	T _J = -	55°C to	175°C	$T_{\rm J} = -5$	5°C to	210°C	UNIT
	PARAME	IEK	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNII
V _{IT+}	Positive- going input threshold voltage		STB at 0 V, See Table 3		800	900		800	900		800	900	
V _{IT}	Negative- going input threshold voltage	High-speed mode	STB at U.V., See Table 3	500	650		500	650		500	650		mV
V_{hys}	Hysteresis voltage (V _{IT+} – V _{IT-})		STB at V _{CC}	100	125		70	125		70	125		
V_{IT}	Input threshold voltage	Standby mode	STB at V _{CC}	500		1150	500		1300	400		1350	
V _{OH}	High-level ou	tput voltage	I _O = -2 mA, See Figure 7	4	4.6		4	4.6		4	4.6		V
V_{OL}	Low-level out	put voltage	I _O = 2 mA, See Figure 7		0.2	0.4		0.2	0.5		0.2	0.55	V
${\rm I}_{\rm I(off)}$	Power-off bus	s input current	CANH or CANL = 5 V, V _{CC} at 0 V, TXD at 0 V			5			15			30	μA
I _{O(off)}	Power-off RX current	D leakage	V _{CC} at 0 V, RXD at 5 V			20			30			30	μA
Cı	Input capacita (CANH or CA	ance to ground, NL)	TXD at 3 V, $V_1 = 0.4 \sin (4E6\pi t) + 2.5 V$		20			20			20		pF
C _{ID}	Differential in	put capacitance	TXD at 3 V, V _I = 0.4 sin (4E6πt)		10			10			10		pF
R _{ID}	Differential in	put resistance	TXD at 3 V, STD at 0 V	30		80	30		80	30		80	
R _{IN}	Input resistan CANL)	ce, (CANH or	TXD at 3 V, STD at 0 V	15	30	40	15	30	40	15	30	40	kΩ
R _{I(m)}	Input resistan [1 – (R _{IN (CANE} 100%	ice matching H) / R _{IN (CANL)})] x	V _{CANH} = V _{CANL}	-3%	0%	3%	-5%	0%	5%	-12%	0%	12%	

RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditiions (unless otherwise noted)

	DADAMETER	TEST CONDITIONS	T _J = -55°C to 125°C			$T_J = -55^{\circ}C$ to 175°C			$T_J = -55$ °C to 210°C			
PARAMETER		TEST CONDITIONS	MIN	MIN TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
t _{pLH}	Propagation delay time, low-to-high-level output		60	100	130	60	100	200	60	100	200	
t _{pHL}	Propagation delay time, high-to-low-level output	STB at 0 V, TXD at 3 V, See Figure 7	45	70	130	45	70	200	45	70	200	ns
t _r	Output signal rise time			8			8			8		
t _f	Output signal fall time			8			8			8		
t _{BUS}	Dominant time required on bus for wake-up from standby ⁽¹⁾	STB at V _{CC} Figure 12	0.7		5	1.0		5.1	1.45		5.25	μs

⁽¹⁾ The device under test shall not signal a wake-up condition with dominant pulses shorter than t_{BUS} (min) and shall signal a wake-up condition with dominant pulses longer than t_{BUS} (max). Dominant pulses with a length between t_{BUS} (min) and t_{BUS} (max) may lead to a wake-up.

SPLIT-PIN CHARACTERISTICS

over recommended operating conditiions (unless otherwise noted)

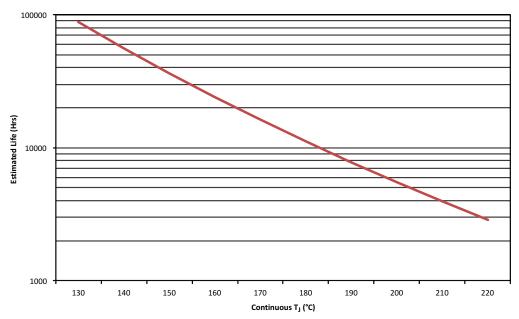
PARAMETER		TEST	T _J = -55°C to 125°C			$T_J = -55^{\circ}C$ to 175°C			T _J = -55°C to 210°C			
		CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
Vo	Output voltage	–500 μA < I _O < 500 μA	0.3×V _{CC}	0.5×V _{CC}	0.7xV _{CC}	0.28×V _{CC}	0.5×V _{CC}	0.7xV _{CC}	0.28×V _C	0.5×V _C	0.7xV _{CC}	V
I _{O(st} b)	Standby mode leakage current	STB at 2 V, –12 V ≤ V _O ≤ 12 V	-5		5	-7		7	-15		15	μA



STB-PIN CHARACTERISTICS

over recommended operating conditiions (unless otherwise noted)

PARAMETER		TEST	T _J = -55°C to 125°C			T _J = -	55°C to 175°C	T _J = -55°C to 210°C			UNIT
		CONDITIONS	MIN	TYP	MAX	MIN	TYP MAX	MIN	TYP	MAX	UNII
I _{IH}	High level input current	STB at 2 V	-10		0	-10	0	-10		0	μA
$I_{\rm IL}$	Low level input current	STB at 0 V	-10		0	-10	0	-10		0	μA



- A. See datasheet for absolute maximum and minimum recommended operating conditions.
- B. Silicon operating life design goal is 10 years at 105°C junction temperature (does not include package interconnect life).
- C. The predicted operating lifetime vs. junction temperature is based on reliability modeling using electromigration as the dominant failure mechanism affecting device wear out for the specific device process and design characteristics.

Figure 1. SN65HVD1040-HT Operating Life Derating Chart



PARAMETER MEASUREMENT INFORMATION

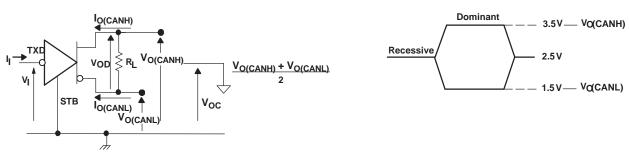
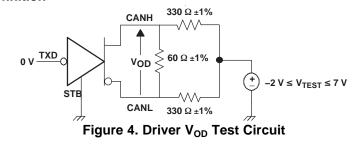


Figure 2. Driver Voltage, Current, and Test Definition

Figure 3. Bus Logic State Voltage Definitions



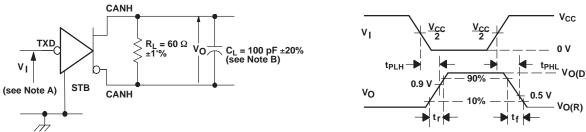


Figure 5. Driver Test Circuit and Voltage Waveforms

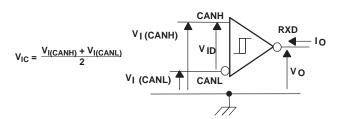
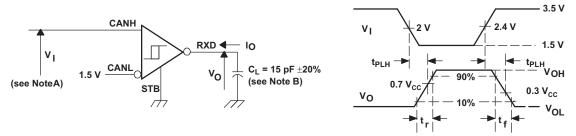


Figure 6. Receiver Voltage and Current Definitions



PARAMETER MEASUREMENT INFORMATION (continued)



- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 125 kHz, 50% duty cycle, $t_r \leq$ 6 ns, $t_f \leq$ 6ns, $Z_O = 50 \Omega$.
- B. C₁ includes instrumentation and fixture capacitance within ±20%.

Open

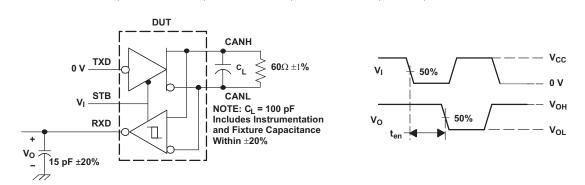
Figure 7. Receiver Test Circuit and Voltage Waveforms

INPUT OUTPUT R V_{CANH} VCANL $|V_{ID}|$ -11.1 V -12 V 900 mV L V_{OL} 12 V 11.1 V 900 mV L -6 V -12 V 6 V L 12 V 6 V 6 V L -11.5 V -12 V 500 mV Н V_{OH} 12 V 11.5 V 500 mV Н -12 V -6 V 6 V Н 6 V 12 V 6 V Н

Χ

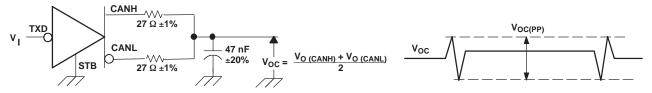
Н

Table 3. Differential Input Voltage Threshold Test



Open

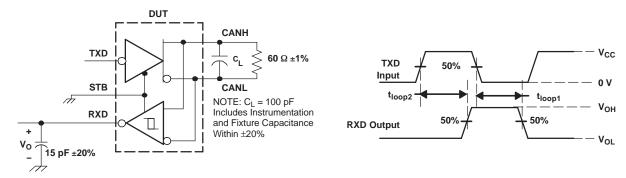
Figure 8. t_{en} Test Circuit and Voltage Waveforms



A. All V_1 input pulses are from 0 V to V_{CC} and supplied by a generator having the following characteristics: t_r or $t_f \le 6$ ns. Pulse Repetition Rate (PRR) = 125 kHz, 50% duty cycle.

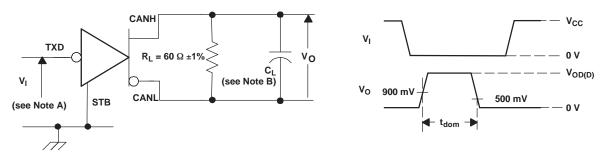
Figure 9. Peak-to-Peak Common Mode Output Voltage Test and Waveform





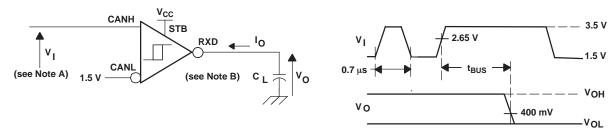
A. All V_1 input pulses are from 0 V to V_{CC} and supplied by a generator with the following characteristics: t_r or $t_f \le 6$ ns. Pulse Repetition Rate (PRR) = 125 kHz, 50% duty cycle.

Figure 10. t_{loop} Test Circuit and Voltage Waveforms



- A. All V_1 input pulses are from 0 V to V_{CC} and supplied by a generator with the following characteristics: t_r or $t_f \le 6$ ns. Pulse Repetition Rate (PRR) = 500 Hz, 50% duty cycle.
- B. $C_L = 100 \text{ pF}$ includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 11. Dominant Time-Out Test Circuit and Waveform



- A. For V_I bit width $\leq 0.7~\mu s$, $V_O = V_{OH}$. For V_I bit width $\geq 5~\mu s$, $V_O = V_{OL}$. V_I input pulses are supplied from a generator with the following characteristics; t_r or $t_f \leq 6$ ns. Pulse Repetition Rate (PRR) = 50 Hz, 30% duty cycle.
- B. $C_L = 15 \text{ pF}$ includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 12. t_{BUS} Test Circuit and Waveform



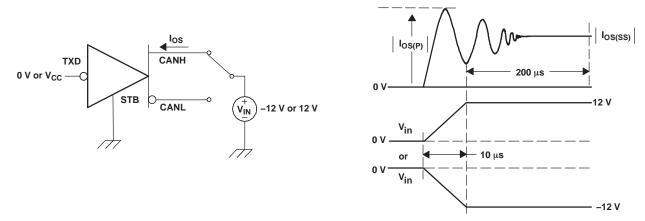


Figure 13. Driver Short-Circuit Current Test and Waveform

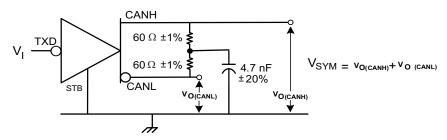


Figure 14. Driver Output Symmetry Test Circuit



DEVICE INFORMATION

Table 4. DRIVER FUNCTION TABLE(1)

INP	UTS	OUTI	PUTS	BUS STATE
TXD	STB	CANH CANL		
L	L	Н	L	DOMINANT
Н	L	Z	Z	RECESSIVE
Open	Х	Z	Z	RECESSIVE
Х	H or Open	Z	Z	RECESSIVE

(1) H = high level; L = low level; X = irrelevant; Z = high impedance

Table 5. RECEIVER FUNCTION TABLE⁽¹⁾

DIFFERENTIAL INPUTS V _{ID} = CANH - CANL	STB	OUTPUT RXD	BUS STATE
V _{ID} ≥ 0.9 V	L	L	DOMINANT
V _{ID} ≥ 1.15 V	H or Open	L	DOMINANT
$0.5 \text{ V} < \text{V}_{\text{ID}} < 0.9 \text{ V}$	X	?	?
V _{ID} ≤ 0.5 V	Х	Н	RECESSIVE
Open	Х	Н	RECESSIVE

(1) H = high level; L = low level; X = irrelevant; ? = indeterminate; Z = high impedance



DEVICE INFORMATION

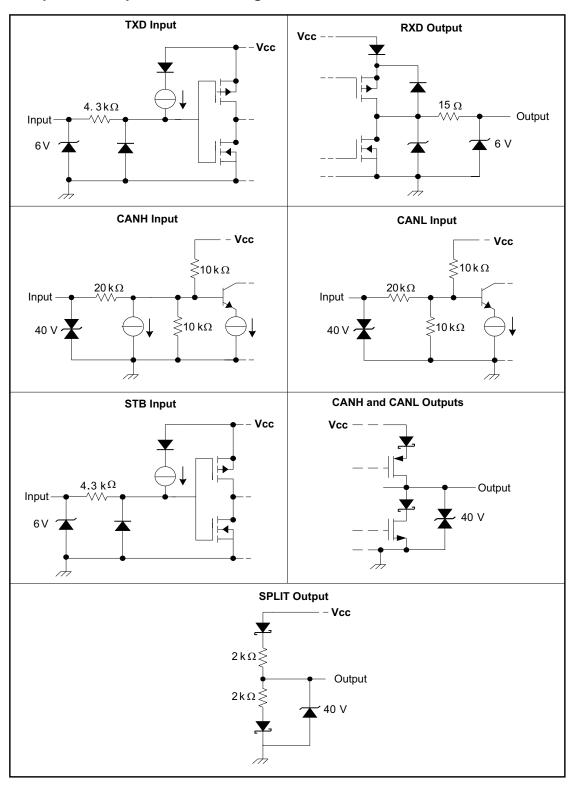
Table 6. Parametric Cross Reference With the TJA1040

TJA1040 ⁽¹⁾	PARAMETER	HVD10xx							
	TJA1040 DRIVER SECTION	•							
V _{IH}	High-level input voltage	Recommended V _{IH}							
V _{IL}	Low-level input voltage	Recommended V _{IL}							
I _{IH}	High-level input current	Driver I _{IH}							
I _{IL}	Low-level input current	Driver I _{IL}							
TJA1040 BUS SECTION									
V _{th(dif)}	Differential input voltage	Receiver V_{IT} and recommended V_{ID}							
V _{hys(dif)}	Differential input hysteresis	Receiver V _{hys}							
$V_{O(dom)}$	Dominant output voltage	Driver V _{O(D)}							
V _{O(reces)}	Recessive output voltage	Driver V _{O(R)}							
$V_{i(dif)(th)}$	Differential input voltage	Receiver V_{IT} and recommended V_{ID}							
V _{O(dif0(bus)}	Differential bus voltage	Driver $V_{OD(D)}$ and $V_{OD(R)}$							
ILI	Power-off bus input current	Receiver I _{I(off)}							
I _{O(SC)}	Short-circuit output current	Driver I _{OS(SS)}							
R _{i(cm)}	CANH, CANL input resistance	Receiver R _{IN}							
R _{i(def)}	Differential input resistance	Receiver R _{ID}							
R _{i(cm) (m)}	Input resistance matching	Receiver R _{I (m)}							
C _{i(cm)}	Input capacitance to ground	Receiver C _I							
C _{i(dif)}	Differential input capacitance	Receiver C _{ID}							
	TJA1040 RECEIVER SECTION								
I _{OH}	High-level output current	Recommended I _{OH}							
I _{OL}	Low-level output current	Recommended I _{OL}							
	TJA1040 SPLIT PIN SECTION								
V _O	Reference output voltage	V _O							
	TJA1040 TIMING SECTION								
t _{d(TXD-BUSon)}	Delay TXD to bus active	Driver t _{PLH}							
t _{d(TXD-BUSoff)}	Delay TXD to bus inactive	Driver t _{PHL}							
t _{d(BUSon-RXD)}	Delay bus active to RXD	Receiver t _{PHL}							
t _{d(BUSoff-RXD)}	Delay bus inactive to RXD	Receiver t _{PLH}							
t _{PD(TXD-RXD)}	Prop delay TXD to RXD	Device t _{LOOP1} and t _{LOOP2}							
t _{d(stb-norm)}	Enable time from standby to dominant	Driver t _{en}							
	TJA1040 STB PIN SECTION								
V _{IH}	High-level input voltage	Recommended V _{IH}							
V _{IL}	Low-level input voltage	Recommended V _{IL}							
I _{IH}	High-level input current	I _{IH}							
I _{IL}	Low-level input current	I _{IL}							

⁽¹⁾ From TJA1040 Product Specification, Philips Semiconductors, 2003 February 19.



Equivalent Input and Output Schematic Diagrams





TYPICAL CHARACTERISTICS

RECESSIVE-TO-DOMINANT LOOP TIME

FREE-AIR TEMPERATURE (across V_{CC})

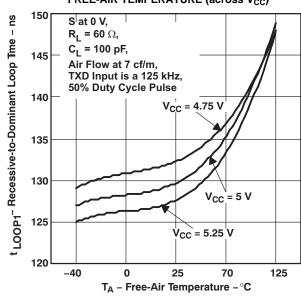
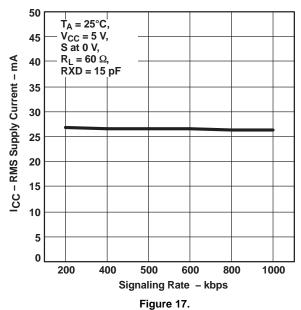


Figure 15.

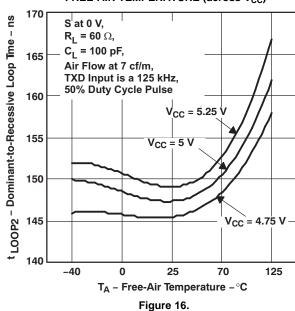
SUPPLY CURRENT (RMS)

SIGNALING RATE



DOMINANT-TO-RECESSIVE LOOP TIME

FREE-AIR TEMPERATURE (across V_{CC})



DRIVER LOW-LEVEL OUTPUT VOLTAGE

vs

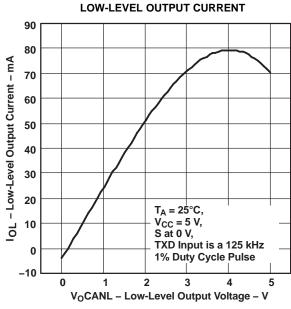


Figure 18.



TYPICAL CHARACTERISTICS (continued)

DRIVER HIGH-LEVEL OUTPUT VOLTAGE

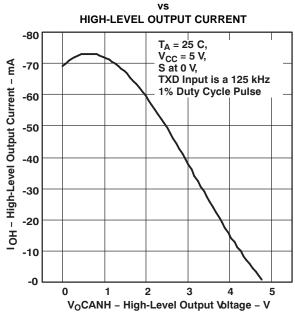


Figure 19.

DRIVER OUTPUT CURRENT

vs SUPPLY VOLTAGE

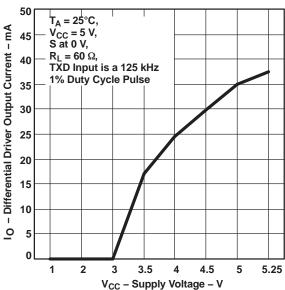


Figure 21.

DRIVER DIFFERENTIAL OUTPUT VOLTAGE

FREE-AIR TEMPERATURE (across V_{CC})

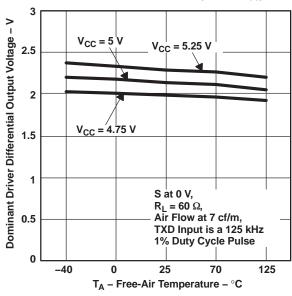


Figure 20.

RECEIVER OUTPUT VOLTAGE

DIFFERENTIAL INPUT VOLTAGE

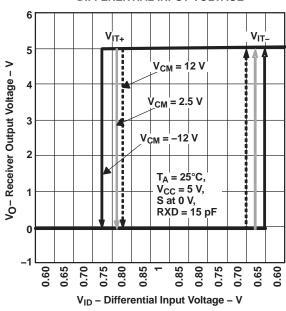


Figure 22.



TYPICAL CHARACTERISTICS (continued)

TYPICAL ELECTROMAGNETIC EMISSIONS UP TO 50 MHZ (Peak Amplitude)

Figure 23. Frequency Spectrum of Common-Mode Emissions

TYPICAL ELECTROMAGNETIC IMMUNITY PERFORMANCE

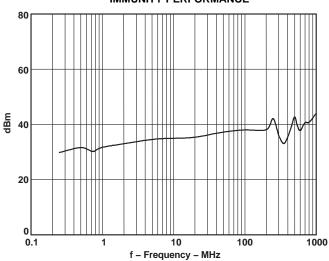


Figure 24. Direct Power Injection (DPI) Response vs Frequency



APPLICATION INFORMATION

CAN Basics

The basics of arbitration require that the receiver at the sending node designate the first bit as dominant or recessive after the initial wave of the first bit of a message travels to the most remote node on a network and back again. Typically, this "sample" is made at 75% of the bit width, and within this limitation, the maximum allowable signal distortion in a CAN network is determined by network electrical parameters.

Factors to be considered in network design include the approximately 5 ns/m propagation delay of typical twisted-pair bus cable; signal amplitude loss due to the loss mechanisms of the cable; and the number, length, and spacing of drop-lines (stubs) on a network. Under strict analysis, variations among the different oscillators in a system also need to be accounted for with adjustments in signaling rate and stub and bus length. Table 7 lists the maximum signaling rates achieved with the SN65HVD1040 with several bus lengths of category 5, shielded twisted pair (CAT 5 STP) cable.

Table 7. Maximum Signaling Rates for Various Cable Lengths

Bus Length (m)	Signaling Rate (kbps)
30	1000
100	500
250	250
500	125
1000	62.5

The ISO 11898 Standard specifies a maximum bus length of 40 m and maximum stub length of 0.3 m with a maximum of 30 nodes. However, with careful design, users can have longer cables, longer stub lengths, and many more nodes to a bus. (Note: Non-standard application may come with a trade-off in signaling rate.) A large number of nodes requires a transceiver with high input impedance such as the HVD1040.

The Standard specifies the interconnect to be a single twisted-pair cable (shielded or unshielded) with 120 Ω characteristic impedance (Z_0). Resistors equal to the characteristic impedance of the line terminate both ends of the cable to prevent signal reflections. Unterminated drop-lines connect nodes to the bus and should be kept as short as possible to minimize signal reflections.

Connectors, while not specified by the standard should have as little effect as possible on standard operating parameters such as capacitive loading. Although unshielded cable is used in many applications, data transmission circuits employing CAN transceivers are usually used in applications requiring a rugged interconnection with a wide common-mode voltage range. Therefore, shielded cable is recommended in these electronically harsh environments, and when coupled with the Standard's –2-V to 7-V common-mode range of tolerable ground noise, helps to ensure data integrity. The HVD1040 enhances the Standard's insurance of data integrity with an extended –12 V to 12 V range of common-mode operation.

ww.ti.com 29-Jun-2012

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
SN65HVD1040HD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-4-260C-72 HR	
SN65HVD1040SHKQ	PREVIEW	CFP	HKQ	8	25	TBD	AU	N / A for Pkg Type	
SN65HVD1040SKGD3	ACTIVE	XCEPT	KGD	0	228	TBD	Call TI	N / A for Pkg Type	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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OTHER QUALIFIED VERSIONS OF SN65HVD1040-HT:

Catalog: SN65HVD1040

Automotive: SN65HVD1040-Q1





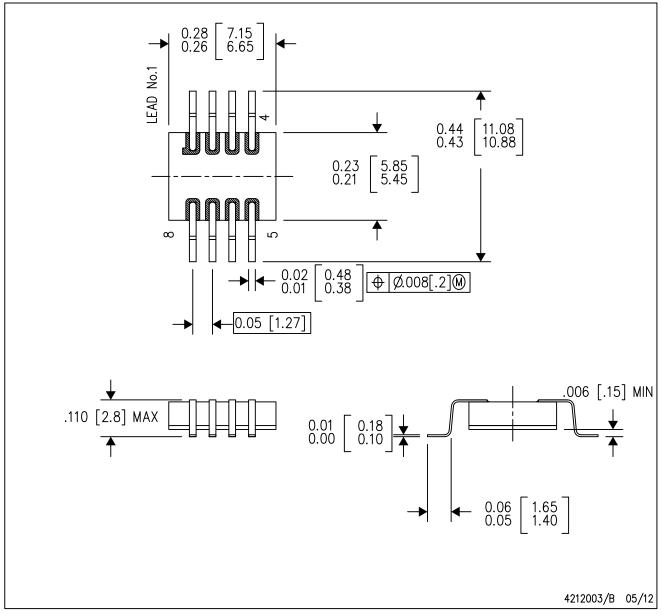
29-Jun-2012

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects

HKQ (R-CDFP-G8)

CERAMIC GULL WING



NOTES:

- All linear dimensions are in inches (millimeters).
- This drawing is subject to change without notice.
- This package can be hermetically sealed with a metal lid.
- D. The terminals will be gold plated.E. Lid is not connected to any lead.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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